

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|------------------------------------|------------------|---------|------------------|
| L1 | 1211 | (optical adj print\$6 adj head) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/05 09:06 |
| L2 | 564 | 1 same (led (light adj emit\$6)) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/05 09:12 |
| L3 | 125 | 2 same lens | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/05 09:12 |
| L4 | 20 | 3 same (photosensitive drum electrostatic) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/05 09:12 |
| L5 | 258 | (optical adj print\$6 adj head) | US-PGPUB; USPAT | OR | ON | 2005/05/05 09:10 |
| L6 | 146 | 5 same (led (light adj emit\$6)) | US-PGPUB; USPAT | OR | ON | 2005/05/05 09:10 |
| L7 | 87 | 6 same (photosensitive drum electrostatic lens) | US-PGPUB; USPAT | OR | ON | 2005/05/05 11:35 |
| L8 | 776 | 1 and (led (light adj emit\$6)) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/05 09:12 |
| L9 | 236 | 8 and lens | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/05 09:12 |
| L10 | 55 | 9 and (photosensitive drum electrostatic) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/05 09:13 |
| L11 | 52 | (rod adj lens adj array) and (photosensitive adj drum) and (transfer adj roller) | US-PGPUB; USPAT | OR | ON | 2005/05/05 10:43 |
| L12 | 16 | (rod adj lens adj array) same clamp same base same hold\$6 | US-PGPUB; USPAT | OR | ON | 2005/05/05 11:36 |
| S1 | 2 | jp-10063807-\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2005/05/03 09:13 |
| S2 | 1524 | (substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) same (adhe\$8 with (semiconductor amorphous polycrystalline polysilicon)) same ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon)) | US-PGPUB; USPAT | OR | ON | 2005/05/04 09:37 |

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|-----|------|--|----------------------------|----|----|------------------|
| S3 | 1406 | (substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 with (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon)) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/04 09:38 |
| S4 | 4 | S3 and (optical adj print\$6 adj head) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/05 09:06 |
| S5 | 3 | S2 and (optical adj print\$6 adj head) | US-PGPUB; USPAT | OR | ON | 2005/05/05 09:10 |
| S6 | 6037 | 257/81.ccls. 257/82.ccls. 257/84.ccls. 257/93.ccls. 257/98.ccls. 257/99.ccls. 257/693.ccls. 257/700.ccls. 257/701.ccls. 257/783.ccls. | US-PGPUB; USPAT | OR | ON | 2005/05/03 09:28 |
| S7 | 148 | S2 and S6 | US-PGPUB; USPAT | OR | ON | 2005/05/03 09:40 |
| S8 | 103 | (substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) with (adhe\$8 near2 (semiconductor amorphous polycrystalline polysilicon)) with ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) near2 (semiconductor device silicon)) | US-PGPUB; USPAT | OR | ON | 2005/05/03 15:21 |
| S9 | 238 | (substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 near2 (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon)) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/03 09:32 |
| S10 | 112 | (substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 near2 (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) near2 (semiconductor device silicon)) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/03 15:33 |

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|-----|-----|---|---|----|-----|------------------|
| S11 | 1 | "6576933".pn. | US-PGPUB; USPAT | OR | OFF | 2005/05/03 15:25 |
| S12 | 1 | "20020030197".pn. | US-PGPUB; USPAT | OR | OFF | 2005/05/03 15:29 |
| S13 | 2 | jp-07065348-\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2005/05/03 15:29 |
| S14 | 212 | (substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) same (adhe\$8 with (amorphous polycrystalline polysilicon)) same ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon)) | US-PGPUB; USPAT | OR | ON | 2005/05/04 09:39 |
| S15 | 150 | (substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 with (amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon)) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/04 09:39 |
| S16 | 67 | (substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) same (adhe\$8 near4 (amorphous polycrystalline polysilicon)) same ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon)) | US-PGPUB; USPAT | OR | ON | 2005/05/04 09:39 |
| S17 | 56 | (substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 near4 (amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon)) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/04 11:35 |
| S18 | 6 | jp-02028315-\$.did. jp-63226914-\$.did. jp-11031828-\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2005/05/04 11:36 |